

Appl. No. 10/783,081  
Reply to Office action of 11/30/2004

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-15 (canceled).

16. (currently amended) A semiconductor structure, comprising:  
a semiconductor substrate having a surface;  
a gate stack outward of the surface of the semiconductor substrate, the gate stack comprising:  
a nitrided silicon oxide layer comprising an oxide layer beneath a nitride layer, wherein the nitride layer has a maximum atomic percentage of nitrogen of between 10 and 20 percent and the oxide layer has a maximum atomic percentage of nitrogen of between 8 and 14 percent;  
a high-K dielectric layer outward of the nitrided silicon oxide layer; and  
a conductive layer outward of the high-K layer;  
sidewall spacers outward of the semiconductor substrate adjacent to the gate stack; and  
source/drain regions in the semiconductor substrate adjacent to the sidewall spacers.

17. (cancelled)

18. (original) The semiconductor structure of Claim 16, wherein a thickness of the nitrided silicon oxide layer is less than about 20 Angstroms.

19. (original) The semiconductor structure of Claim 16, wherein the high-K dielectric layer comprises an oxygen-containing material.

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20. (original) The semiconductor structure of Claim 16, wherein the high-K dielectric layer comprises a material selected from the group consisting of  $Ta_2O_5$ ,  $BaTiO_3$ ,  $TiO_2$ ,  $CeO_2$ , and barium strontium titanate.